

# Semiconductor Electronics

## NCERT Examples

Ex. 1 For semiconductors, bandgap energy  $E_g < 3 \text{ eV}$ .  
 For carbon,  $E_g \sim 5.5 \text{ eV}$ , for Si,  $E_g \sim 1.1 \text{ eV}$  and for Ge,  $E_g \sim 0.66 \text{ eV}$ .

Here  $E_g$  for carbon ( $5.5 \text{ eV}$ )  $> 3 \text{ eV}$ . So carbon is an insulator but the values of  $E_g$  for Si and Ge are less than  $3 \text{ eV}$  so these are semiconductors.

OR

Due to the higher value of  $E_g$  for carbon ( $5.5 \text{ eV}$ ), Energy required to take out an electron from carbon atom is much higher, hence no. of free electrons are negligibly small in carbon which makes it an insulator.

Ex. 2 Given,

$$N_{\text{Si}} = 5 \times 10^{20} \text{ atoms/m}^3$$

doping concentration of As,

$$1 \text{ ppm} = \frac{1}{10^6}$$

$$\text{So no. of donor atoms } N_D = \frac{N_{\text{Si}}}{10^6}$$

$$= \frac{5 \times 10^{20}}{10^6}$$

$$N_D = 5 \times 10^{14} \text{ atoms/m}^3$$

$$n_i = 1.5 \times 10^{16} \text{ m}^{-3} \text{ (intrinsic carrier concentration)}$$

$$n_e = ? \quad n_h = ?$$

for no. of electrons,  $n_e$   
here  $N_D \approx n_e$   
so  $n_e = 5 \times 10^{22} \text{ m}^{-3}$  A<sub>2</sub>

for no. of holes,  $n_h$

$$\text{by } n_i^2 = n_e n_h$$

$$n_h = \frac{n_i^2}{n_e} = \frac{(1.5 \times 10^{16})^2}{5 \times 10^{22}}$$

$$= \frac{0.3}{5} \times 1.5 \times 10^{32-22}$$

$$= 0.45 \times 10^{10}$$

$$n_h = 4.5 \times 10^9 \text{ m}^{-3}$$
 A<sub>1</sub>

Ex-3. No, we cannot create p-n junction by joining slabs of p-type and n-type semiconductors, physically because the surfaces of slabs have roughness much larger than atomic spacing ( $2 \text{ \AA}$  to  $3 \text{ \AA}$ ). This prevents atomic level continuity, so the interface acts like a barrier to charge carriers and the depletion region will not form.

Ex-4. consider the graph as a straight line b/w  $I = 10 \text{ mA}$  to  $I = 20 \text{ mA}$ . [ $1 \text{ mA} = 10^{-3} \text{ A}$ ]

(a) Now the dynamic resistance, for,  $V = 0.7 \text{ V}$  to  $0.8 \text{ V}$

$$\begin{aligned} (r_d)_{F.B} &= \frac{\Delta V}{\Delta I} = \frac{0.8 - 0.7}{(20 - 10) \times 10^{-3}} \\ &= \frac{0.1}{10 \times 10^{-3}} \end{aligned}$$

$$= 0.1 \times 10^2$$

$$(R_d)_{FB} = 10 \, \Omega \quad \underline{A_n}$$

(b) From the curve at  $v = -10 \text{ V}$ ,  $I = -1 \mu\text{A}$

$$I = -1 \times 10^{-6} \text{ A}$$

$$(R_d)_{RB} = \frac{V}{I} \quad [I \text{ constant}]$$

$$= \frac{-10}{-1 \times 10^{-6}}$$

$$= 10 \times 10^6$$

$$(R_d)_{RB} = 10^7 \, \Omega$$

A\_n

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